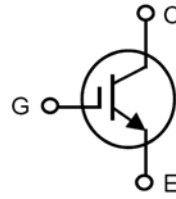


# 900V XPT™ IGBT GenX3™

## IXYY8N90C3 IXYP8N90C3

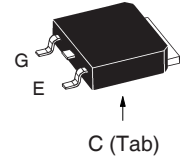
High-Speed IGBT  
for 20-50 kHz Switching



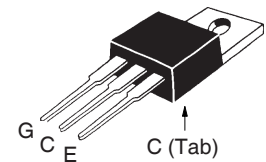
$V_{CES} = 900V$   
 $I_{C110} = 8A$   
 $V_{CE(sat)} \leq 3.0V$   
 $t_{fi(typ)} = 130ns$

Symbol	Test Conditions	Maximum Ratings	
$V_{CES}$	$T_J = 25^\circ C$ to $175^\circ C$	900	V
$V_{CGR}$	$T_J = 25^\circ C$ to $175^\circ C$ , $R_{GE} = 1M\Omega$	900	V
$V_{GES}$	Continuous	$\pm 20$	V
$V_{GEM}$	Transient	$\pm 30$	V
$I_{C25}$	$T_C = 25^\circ C$	20	A
$I_{C110}$	$T_C = 110^\circ C$	8	A
$I_{CM}$	$T_C = 25^\circ C$ , 1ms	48	A
$I_A$	$T_C = 25^\circ C$	4	A
$E_{AS}$	$T_C = 25^\circ C$	15	mJ
<b>SSOA</b> <b>(RBSOA)</b>	$V_{GE} = 15V$ , $T_{VJ} = 150^\circ C$ , $R_G = 30\Omega$ Clamped Inductive Load	$I_{CM} = 16$ @ $V_{CE} \leq V_{CES}$	A
$P_C$	$T_C = 25^\circ C$	125	W
$T_J$		-55 ... +175	$^\circ C$
$T_{JM}$		175	$^\circ C$
$T_{stg}$		-55 ... +175	$^\circ C$
$T_L$	Maximum Lead Temperature for Soldering	300	$^\circ C$
$T_{SOLD}$	1.6 mm (0.062in.) from Case for 10s	260	$^\circ C$
$M_d$	Mounting Torque (TO-220)	1.13/10	Nm/lb.in.
<b>Weight</b>	TO-252	0.35	g
	TO-220	3.00	g

### TO-252 (IXYY)



### TO-220 (IXYP)



G = Gate      C = Collector  
E = Emitter    Tab = Collector

### Features

- Optimized for Low Switching Losses
- Square RBSOA
- Positive Thermal Coefficient of  $V_{ce(sat)}$
- Avalanche Rated
- International Standard Packages

### Advantages

- High Power Density
- Low Gate Drive Requirement

### Applications

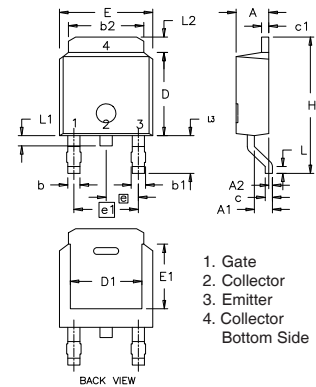
- High Frequency Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines
- Lamp Ballasts

Symbol	Test Conditions ( $T_J = 25^\circ C$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{CES}$	$I_C = 250\mu A$ , $V_{GE} = 0V$	950		V
$V_{GE(th)}$	$I_C = 250\mu A$ , $V_{CE} = V_{GE}$	3.5		6.0 V
$I_{CES}$	$V_{CE} = V_{CES}$ , $V_{GE} = 0V$ $T_J = 150^\circ C$			10 $\mu A$ 150 $\mu A$
$I_{GES}$	$V_{CE} = 0V$ , $V_{GE} = \pm 20V$			$\pm 100$ nA
$V_{CE(sat)}$	$I_C = 8A$ , $V_{GE} = 15V$ , Note 1 $T_J = 150^\circ C$	2.15 2.75		3.00 V V

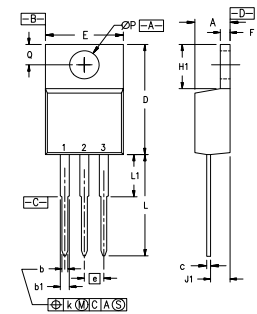
Symbol Test Conditions		Characteristic Values		
(T <sub>J</sub> = 25°C Unless Otherwise Specified)		Min.	Typ.	Max.
<b>g<sub>fs</sub></b>	I <sub>C</sub> = 8A, V <sub>CE</sub> = 10V, Note 1	2.9	4.8	S
<b>C<sub>ies</sub></b>	V <sub>CE</sub> = 25V, V <sub>GE</sub> = 0V, f = 1MHz		400	pF
<b>C<sub>oes</sub></b>			24	pF
<b>C<sub>res</sub></b>			7.8	pF
<b>Q<sub>g(on)</sub></b>	I <sub>C</sub> = 8A, V <sub>GE</sub> = 15V, V <sub>CE</sub> = 0.5 • V <sub>CES</sub>		13.3	nC
<b>Q<sub>ge</sub></b>			3.4	nC
<b>Q<sub>gc</sub></b>			5.8	nC
<b>t<sub>d(on)</sub></b>	<b>Inductive load, T<sub>J</sub> = 25°C</b> I <sub>C</sub> = 8A, V <sub>GE</sub> = 15V V <sub>CE</sub> = 0.5 • V <sub>CES</sub> , R <sub>G</sub> = 30Ω		16	ns
<b>t<sub>ri</sub></b>			20	ns
<b>E<sub>on</sub></b>			0.46	mJ
<b>t<sub>d(off)</sub></b>			40	ns
<b>t<sub>fi</sub></b>		Note 2	130	ns
<b>E<sub>off</sub></b>		0.18	0.50	mJ
<b>t<sub>d(on)</sub></b>	<b>Inductive load, T<sub>J</sub> = 125°C</b> I <sub>C</sub> = 8A, V <sub>GE</sub> = 15V V <sub>CE</sub> = 0.5 • V <sub>CES</sub> , R <sub>G</sub> = 30Ω		17	ns
<b>t<sub>ri</sub></b>			22	ns
<b>E<sub>on</sub></b>			1.00	mJ
<b>t<sub>d(off)</sub></b>			75	ns
<b>t<sub>fi</sub></b>		Note 2	163	ns
<b>E<sub>off</sub></b>		0.22	mJ	
<b>R<sub>thJC</sub></b>				1.20 °C/W
<b>R<sub>thCS</sub></b>	TO-252	0.35		°C/W
	TO-220	0.50		°C/W

**Notes:**

1. Pulse test, t ≤ 300μs, duty cycle, d ≤ 2%.
2. Switching times & energy losses may increase for higher V<sub>CE</sub>(clamp), T<sub>J</sub> or R<sub>G</sub>.

**TO-252 AA Outline**


Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	2.19	2.38	0.086	0.094
A1	0.89	1.14	0.035	0.045
A2	0	0.13	0	0.005
b	0.64	0.89	0.025	0.035
b1	0.76	1.14	0.030	0.045
b2	5.21	5.46	0.205	0.215
c	0.46	0.58	0.018	0.023
c1	0.46	0.58	0.018	0.023
D	5.97	6.22	0.235	0.245
D1	4.32	5.21	0.170	0.205
E	6.35	6.73	0.250	0.265
E1	4.32	5.21	0.170	0.205
e	2.28 BSC		0.090 BSC	
e1	4.57 BSC		0.180 BSC	
H	9.40	10.42	0.370	0.410
L	0.51	1.02	0.020	0.040
L1	0.64	1.02	0.025	0.040
L2	0.89	1.27	0.035	0.050
L3	2.54	2.92	0.100	0.115

**TO-220 Outline**


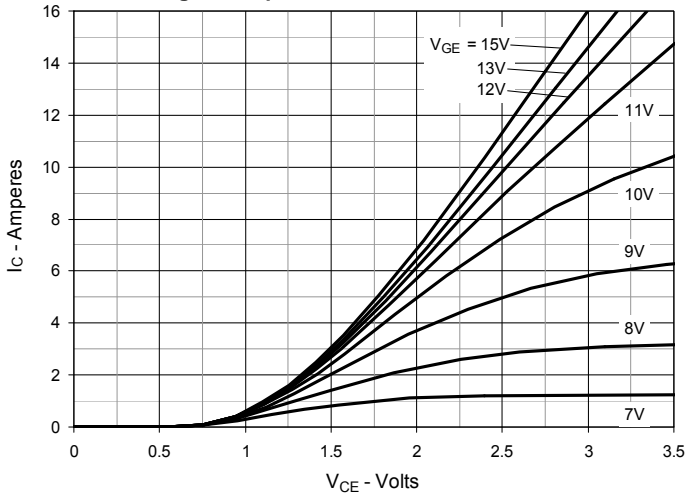
Pins: 1 - Gate      2 - Collector  
3 - Emitter

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.170	.190	4.32	4.83
b	.025	.040	0.64	1.02
b1	.045	.065	1.15	1.65
c	.014	.022	0.35	0.56
D	.580	.630	14.73	16.00
E	.390	.420	9.91	10.66
e	.100 BSC		2.54 BSC	
F	.045	.055	1.14	1.40
H1	.230	.270	5.85	6.85
J1	.090	.110	2.29	2.79
k	0	.015	0	0.38
L	.500	.550	12.70	13.97
L1	.110	.230	2.79	5.84
ØP	.139	.161	3.53	4.08
Q	.100	.125	2.54	3.18

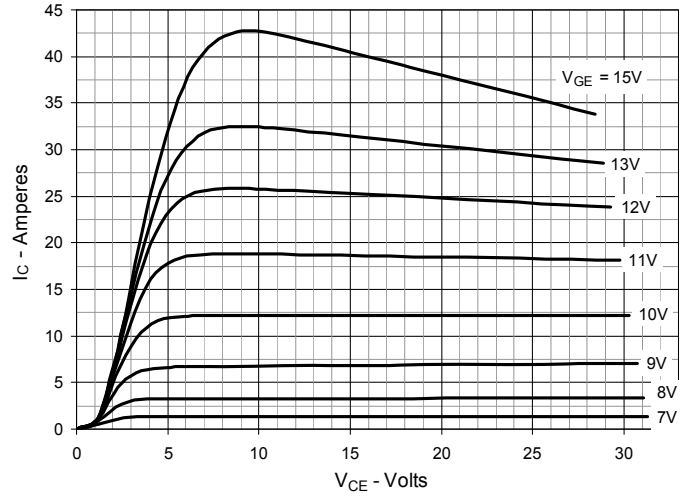
IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

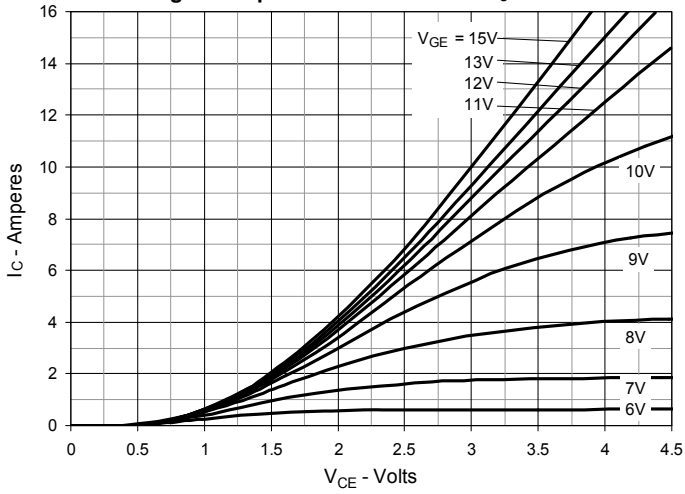
**Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$**



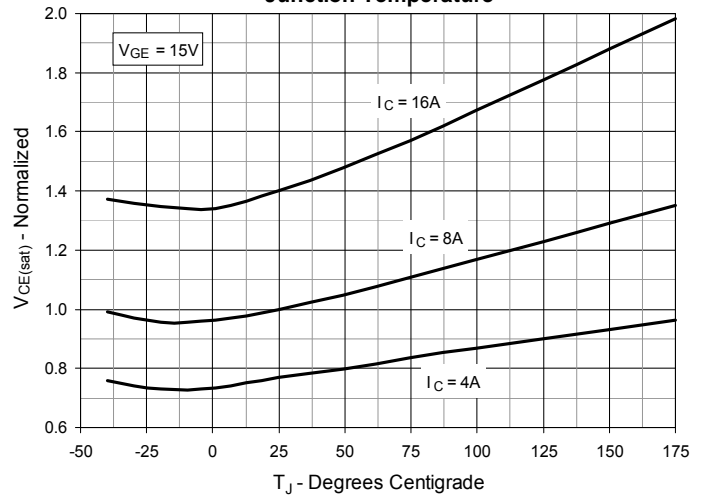
**Fig. 2. Extended Output Characteristics @  $T_J = 25^\circ\text{C}$**



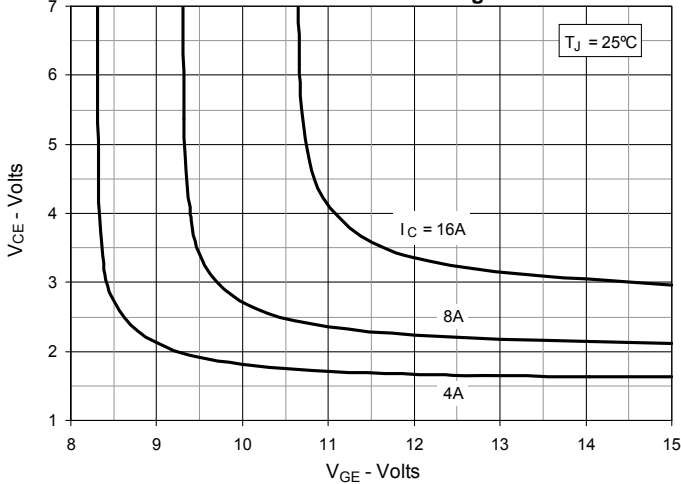
**Fig. 3. Output Characteristics @  $T_J = 150^\circ\text{C}$**



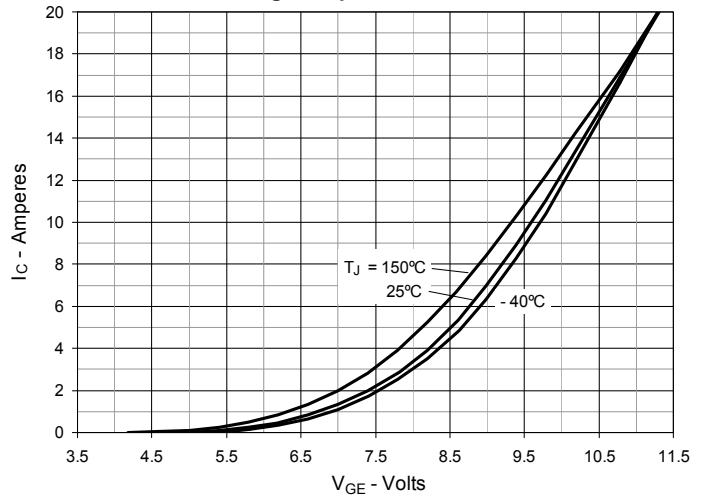
**Fig. 4. Dependence of  $V_{CE(sat)}$  on Junction Temperature**



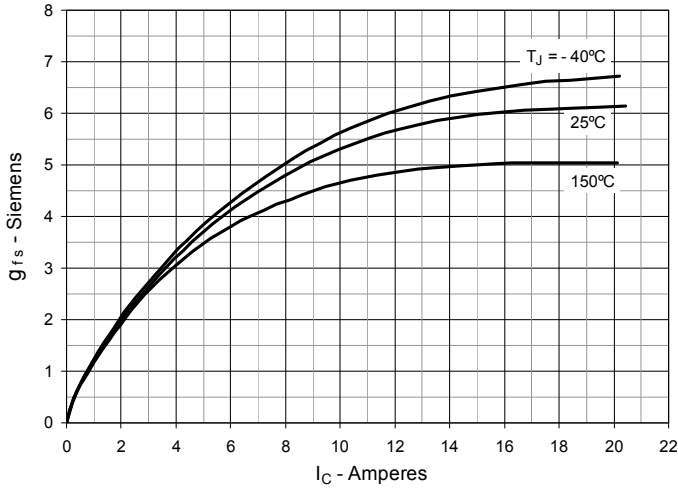
**Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage**



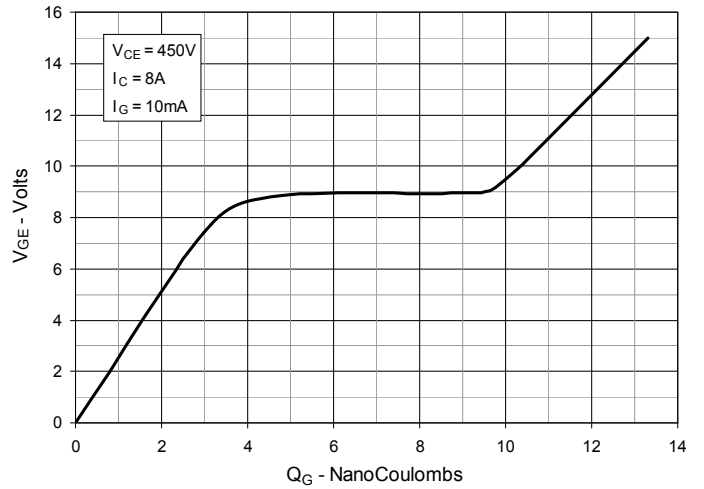
**Fig. 6. Input Admittance**



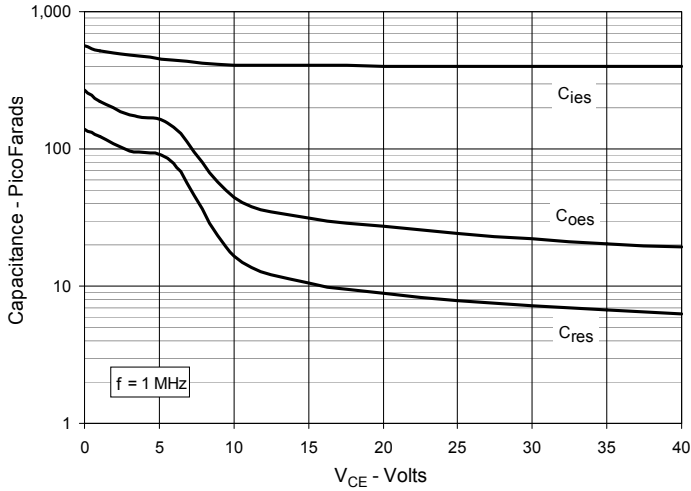
**Fig. 7. Transconductance**



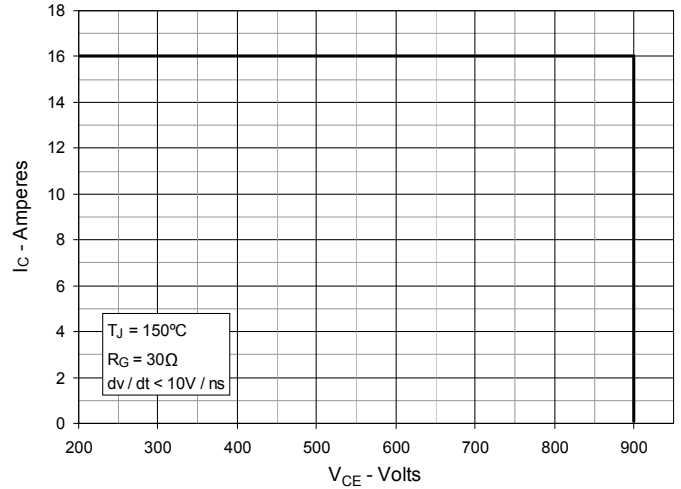
**Fig. 8. Gate Charge**



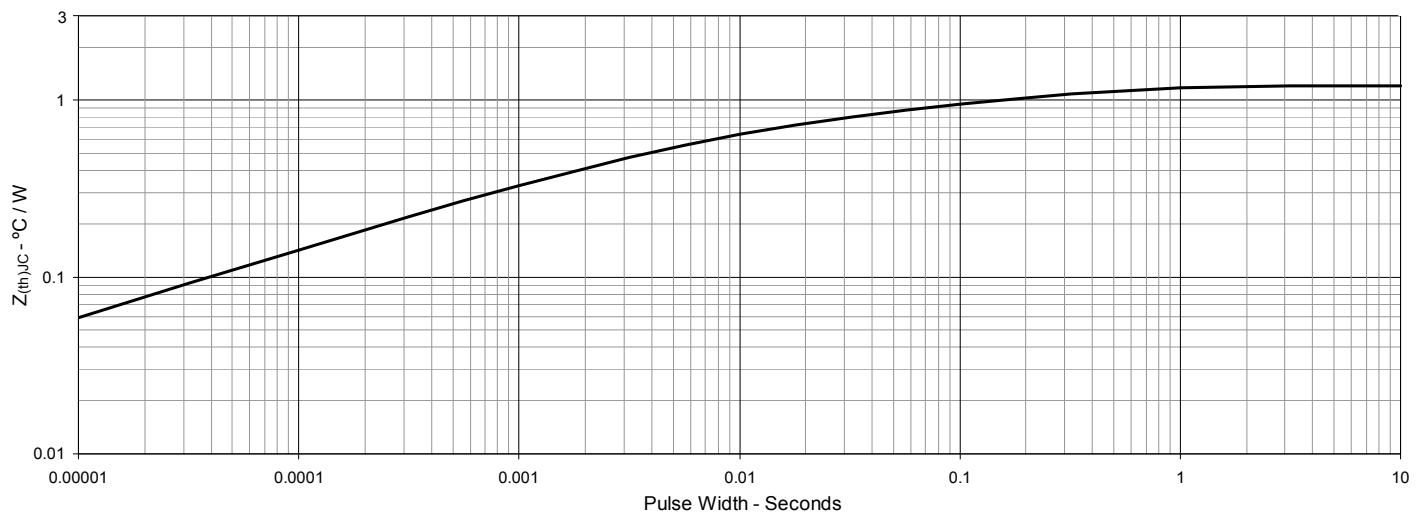
**Fig. 9. Capacitance**



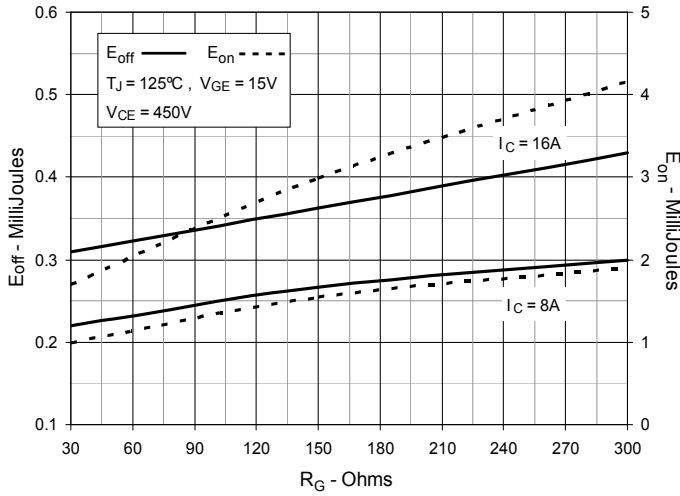
**Fig. 10. Reverse-Bias Safe Operating Area**



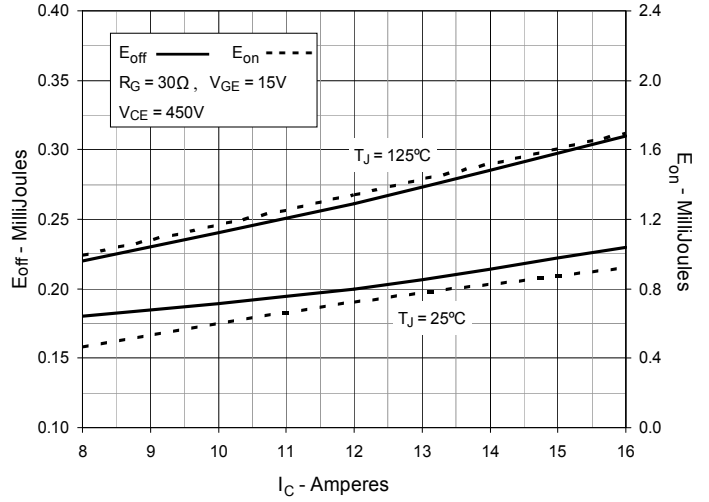
**Fig. 11. Maximum Transient Thermal Impedance**



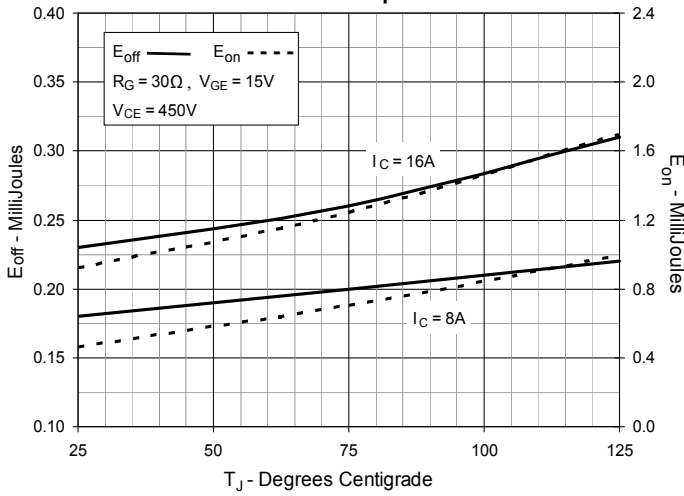
**Fig. 12. Inductive Switching Energy Loss vs. Gate Resistance**



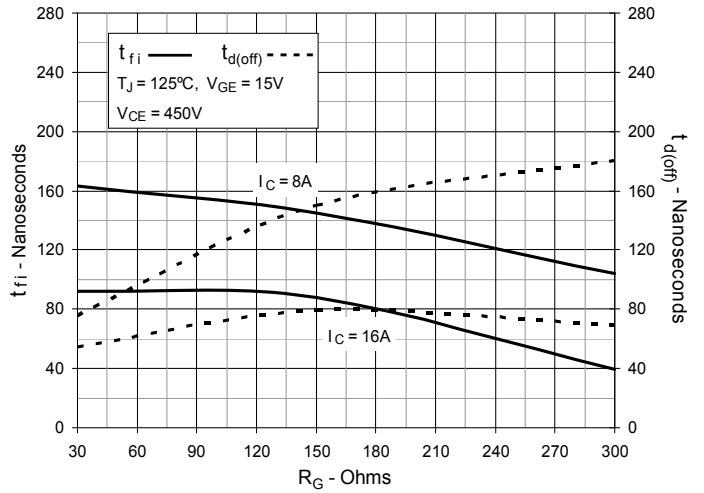
**Fig. 13. Inductive Switching Energy Loss vs. Collector Current**



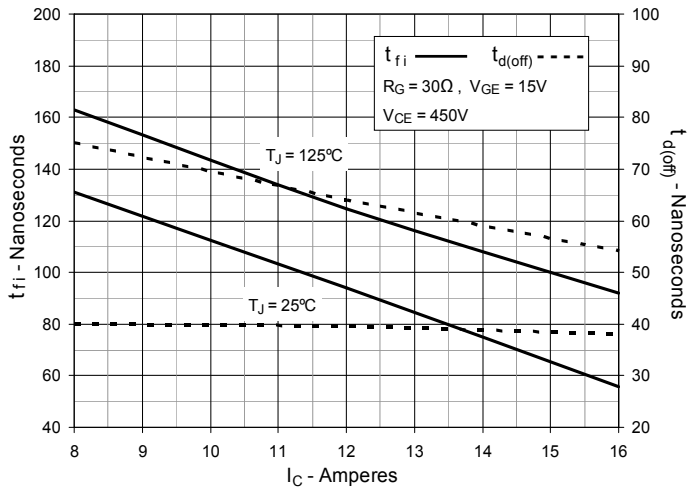
**Fig. 14. Inductive Switching Energy Loss vs. Junction Temperature**



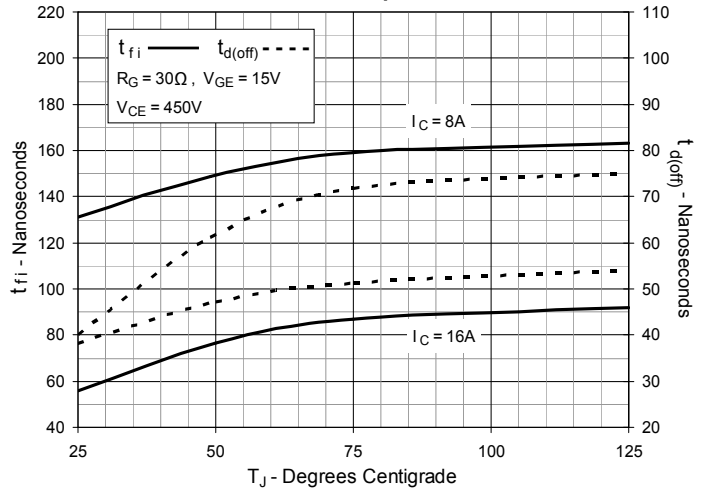
**Fig. 15. Inductive Turn-off Switching Times vs. Gate Resistance**



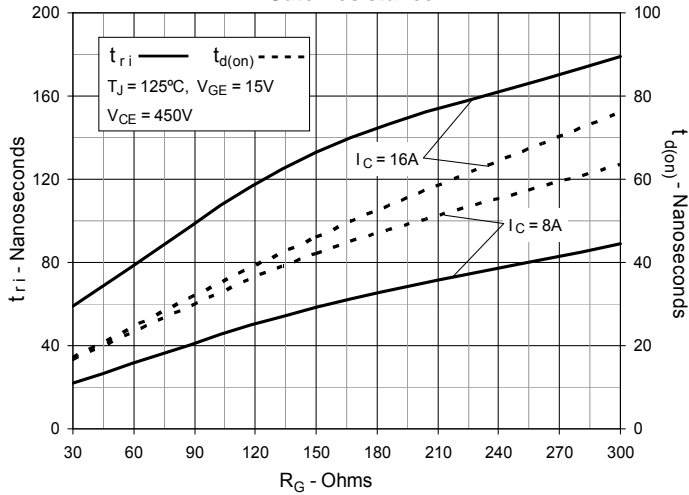
**Fig. 16. Inductive Turn-off Switching Times vs. Collector Current**



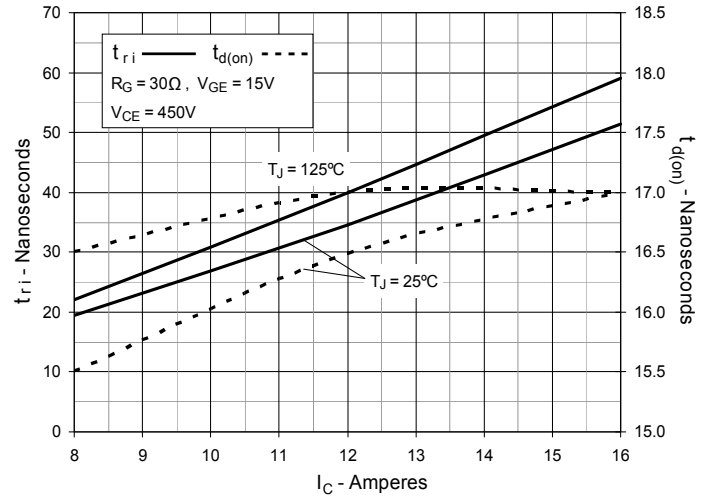
**Fig. 17. Inductive Turn-off Switching Times vs. Junction Temperature**



**Fig. 18. Inductive Turn-on Switching Times vs. Gate Resistance**



**Fig. 19. Inductive Turn-on Switching Times vs. Collector Current**



**Fig. 20. Inductive Turn-on Switching Times vs. Junction Temperature**

